UNIKC Semiconductor

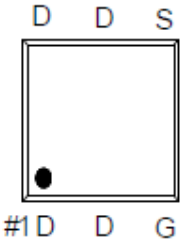
RoHS Compliant

P1603BEB

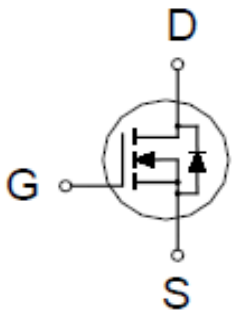
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D[3]
30V	16mΩ @V_{GS} = 10V	21A



PDFN 2X2S



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current[3]	T_C = 25 °C	I_D	21	A
	T_C = 100 °C		17	
	T_A = 25 °C		8	
	T_A= 70 °C		6	
Pulsed Drain Current[1]		I_{DM}	60	
Avalanche Current		I_{AS}	18	
Avalanche Energy	L = 0.1 mH	E_{AS}	16	mJ
Power Dissipation	T_C = 25 °C	P_D	16	W
	T_C = 100 °C		10	
	T_A= 25 °C		2	
	T_A= 70°C		1.2	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	$R_{\theta JA}$		65	°C / W
Junction-to-Case	$R_{\theta JC}$		7.6	

[1]Pulse width limited by maximum junction temperature.

[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Coppe.

[3]Package limitation current is 12A.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1	1.7	2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =24V, V_{GS} = 0V			1	μA
		V_{DS} =20V, V_{GS} = 0V, T_J = 125°C			10	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 10V, V_{GS} = 10V	55			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 5A		22	25	mΩ
		V_{GS} =10V, I_D = 7A		13	16	
Forward Transconductance[1]	g_{fs}	V_{DS} =10V, I_D = 7A		35		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		560		pF
Output Capacitance	C_{oss}			130		
Reverse Transfer Capacitance	C_{rss}			75		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		1.5		Ω
Total Gate Charge[2]	$Q_{g(VGS=10V)}$	V_{DS} = 0.5$V_{(BR)DSS}$, I_D = 7A		12		nC
	$Q_{g(VGS=4.5V)}$			6		
Gate-Source Charge[2]	Q_{gs}			2.1		
Gate-Drain Charge[2]	Q_{gd}			3.5		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 15V $I_D \cong$ 7A, V_{GEN} = 10V, R_G = 6Ω		7		nS
Rise Time[2]	t_r			29		
Turn-Off Delay Time[2]	$t_{d(off)}$			45		
Fall Time[2]	t_f			18		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				21	A
Forward Voltage[1]	V_{SD}	I_F = 7A, V_{GS} = 0V			1	V
Reverse Recovery Time	t_{rr}	I_F = 7A, dI_F/dt = 100A / μS		24		nS
Reverse Recovery Charge	Q_{rr}			29		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

[3]Package limitation current is 12A.

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Package Dimension

PDFN 2x2S MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	1.9		2.1	I	0		0.05
B	1.9		2.1	J		0.203	
C	0.55	0.65	0.75	K	0.55		0.8
D	0.85		1.25	L	0.2		0.4
E	0.174	0.25	0.326	M	0.46		0.85
F	0.25		0.35	N		0.15	
G		0.2		O		0.23	
H	0.8		1.15